

## Silicon NPN Power Transistors

2SD792

## DESCRIPTION

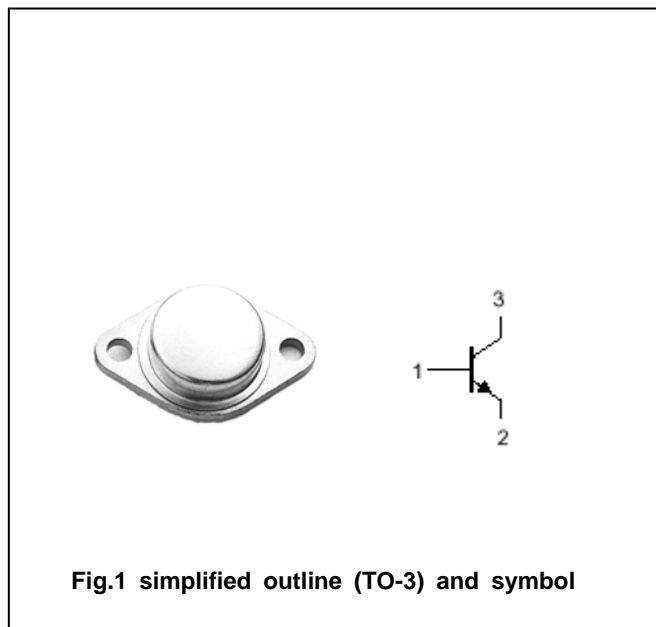
- With TO-3 package
- High voltage
- Wide area of safe operation

## APPLICATIONS

- For line-operated horizontal deflection output applications

## PINNING(see fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector



## Absolute maximum ratings(Ta=°C)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V <sub>CBO</sub>	Collector-base voltage	Open emitter	1500	V
V <sub>CEO</sub>	Collector-emitter voltage	Open base	700	V
V <sub>EBO</sub>	Emitter-base voltage	Open collector	4	V
I <sub>C</sub>	Collector current		5	A
I <sub>CM</sub>	Collector current-peak		7	A
P <sub>T</sub>	Total power dissipation	T <sub>C</sub> =90°C	35	W
T <sub>j</sub>	Junction temperature		150	°C
T <sub>stg</sub>	Storage temperature		-55~150	°C

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## CHARACTERISTICS

T<sub>j</sub>=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>CEO(SUS)</sub>	Collector-emitter sustaining voltage	I <sub>C</sub> =0.1A; I <sub>B</sub> =0; L=25mH	700			V
V <sub>(BR)EBO</sub>	Emitter-base breakdown voltage	I <sub>E</sub> =10mA; I <sub>C</sub> =0	4			V
V <sub>CEsat</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =4.5 A; I <sub>B</sub> =2 A			1.5	V
V <sub>BEsat</sub>	Base-emitter saturation voltage	I <sub>C</sub> =4.5 A; I <sub>B</sub> =2 A			1.5	V
I <sub>CBO</sub>	Collector cut-off current	V <sub>CB</sub> =750V; I <sub>E</sub> =0			50	μ A
		V <sub>CB</sub> =1500V; I <sub>E</sub> =0			1.0	mA
I <sub>EBO</sub>	Emitter cut-off current	V <sub>EB</sub> =4V; I <sub>C</sub> =0			0.1	mA
h <sub>FE</sub>	DC current gain	I <sub>C</sub> =4A ; V <sub>CE</sub> =10V	4		12	
t <sub>f</sub>	Fall time	I <sub>C</sub> =4A; I <sub>BEnd</sub> =1.8A; L <sub>B</sub> =10 μ H			0.7	μ s
t <sub>stg</sub>	Storage time			13		μ s

PACKAGE OUTLINE

